INTEGRATED CIRCUIT **TOSHIBA** TECHNICAL DATA

TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT **TA7688F**

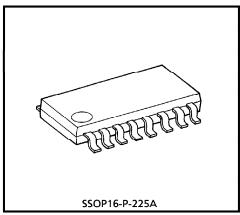
SILICON MONOLITHIC

STEREO HEADPHONE AMPLIFIER (3V USE)

The TA7688F is a stereo headphone power amplifier IC designed for portable cassette player applications.

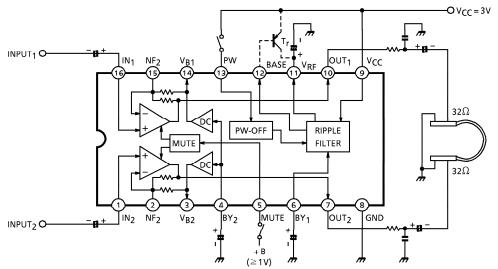
FEATURES

- Small installed area and few external parts
- Low supply current : I_{CCO} = 7mA (Typ.) at 3V
- Built-in a ripple filter
- Built-in a power amplifier mute
- Built-in a power off circuit
- Operating supply voltage range: V_{CC}(opr) = 1.8~5V
- Recommended supply voltage $: V_{CC} = 3V$
- The standard model is TA7688F (SO)

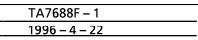


Weight: 0.14g (Typ.)

BLOCK DIAGRAM



Dotted Line is an additional circuit to boost the stabilized current. (Option)



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APPLICATION NOTE

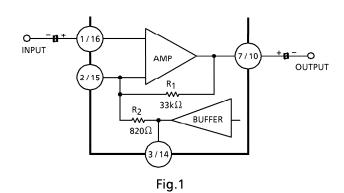
1. Voltage gain adjustment

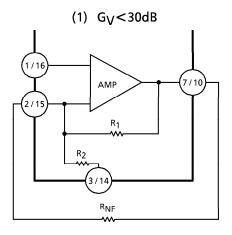
The closed loop Voltage gain G_V is determined by the ratio of R_1 and R_2 shown in Fig.1.

$$G_V = 20 \ell og \frac{R_1 + R_2}{R_2} = 32 dB$$

But the actual value is 30.5dB because of influence of the other circuit.

Fig.2 showes the application circuit of higher or lower gain than recommended one.





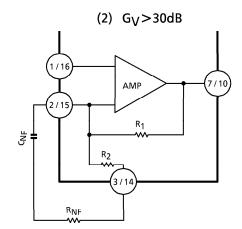


Fig.2

In the case of G_V < 30dB, it happens to oscillate by phase delay at high frequency.

So this IC is not available at G_V <30dB. In the case of G_V >30dB, input offset is amplified, so that output DC voltage differs from center voltage. The unsymmetrical clipping wave is prevented by inserting capacitor C_{NF} .

Therefore this IC is available at G_V>30dB by using C_{NF}.

It is recommended to check pop noise based on CNF.

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2. Muting

Muting operates when the voltage is applied to pin 5 or the current is flowed into pin 5.

Supply current is about half at muting ON.

It is necessary that muting drive current IMUTE is less than 150 μ A.

3. Oscillation precaution

(1) Oscillation preventing capacitor between output pin and GND is recommended to use capacitor with less temperature drift. So suitable capacitor is not celamic or electrolytic capacitor, but tantalum or polyester film capacitor.

When protector resistor 3.9 Ω is rejected, output power increases. In this case, it is necessary to insert 3.9 Ω as shown in Fig.4. When R_L = 0, output current is very large in the circuit.

- (2) It is necessary to use tantalum capacitor at Pin 11 (22 μ F) .
- (3) Decoupling capacitor C₁₀ is necessary to be near the pin 9.

4. Radiation precaution

Because of wide band (about 200kHz), the radiation from the amplifier degrade S/N at radio. As shown in Fig.5, it recommended to limit the band by C and R. In this case, phase compensation check is necessary. When C = 100pF, R = 15k Ω , fHC is 30~50kHz.

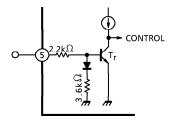


Fig.3

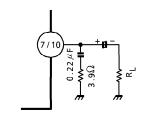
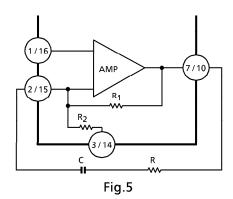


Fig.4



MAXIMUM RATINGS ($Ta = 25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	Vcc	7	V
Output Current	lo	160 / ch	mA
Filter Output Current	I _R	10	mA
Power Dissipation (Note)	PD	350	mW
Operating Temperature	T _{opr}	- 25∼75	°C
Storage Temperature	T _{stg}	- 55∼150	°C

Note : Derated above $Ta = 25^{\circ}C$ in the proportion of $2.8 \text{mW}/^{\circ}C$.

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INTEGRATED CIRCUIT **TOSHIBA**

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ELECTRICAL CHARACTERISTICS

(Unless otherwise specified, Ta = 25°C, V_{CC} = 3V, R_g = 600 Ω , f = 1kHz) $R_H = 3.9\Omega$, $R_L = 32\Omega$ 1. AC characteristics

CHARACTERISTIC		SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Quiescent C	urront	ICCQ (1)		V _{in} = 0		7	12	mA
Quiescent	urrent	ICCQ (2)		$V_{in} = 0$, SW_2 : OFF	_	1	10	μ A
Output Pow	(Or			THD = 10%	20	27	—	mW
Cutput Fow	(C)	P _o (2)		$R_L = 16\Omega$, THD = 10%	_	38	_	11100
Total Harmo	onic Distortion	THD	_	$P_0 = 10 \text{mW} / \text{ch}$		0.12	1.0	%
Closed Loop	Voltage Gain	GV	_	$V_{in} = -42dBV$	28.5	30.5	32.5	dB
Channel Bal	ance	⊿Gy	_	$V_{in} = -42 dBV$		0	± 1	dB
Cross Talk		СТ	_	$V_0 = -2 dBV, ch1 \leftrightarrow ch2$	45	65	_	dB
Ripple	Headphone AMP	RR (1)	_	$f_r = 1kHz$, $V_r = -22dBV$	30	45	_	dB
Rejection	Ripple Filter	RR (2)	_	$f_r = 100Hz, V_r = -22dBV$	_	40	—	dB
Output Noise Voltage		V _{no}	_	BPF = 20Hz~20kHz	_	0.06	0.2	mV _{rms}
Input Resistance		R _{IN}	_	f = 1kHz	15	20	25	$\mathbf{k}\Omega$
		V _{RF} (1)		$V_{CC} = 2V$, $I_{RF} = 10$ mA	1.45	1.6	_	
Ripple Filter Output Voltage		V _{RF} (2)	 	I _{RF} = 10mA	2.1	2.3	2.5	V
		VRF (3)		$V_{CC} = 4.5V$, $I_{RF} = 10mA$	_	3.4	—	
Muting Attenuation		ATT	_	$V_{MUTE} = 3V (0dB = 240mV_{rms})$	60	80	_	dB
Muting Input Voltage		VMUTE	_	$ATT \ge 50dB (0dB = 240mV_{rms})$	_	0.7	1.0	V
Muting Input Current		IMUTE	_	$ATT \ge 50dB (0dB = 240mV_{rms})$	_	35	_	μΑ
Ripple Filter Current		ΙΒ	_	_	_	0.05	_	mA

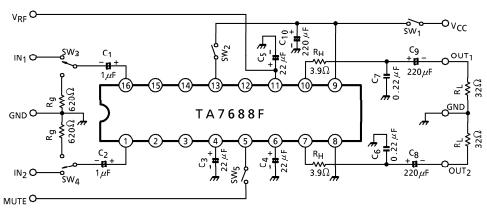
2. DC characteristics (Ta = 25° C, V_{CC} = 3V, Terminal voltage at no signal)

ITEM	SYMBOL	RATING	UNIT
Terminal 1 (IN ₂)	٧1	1.5	V
2 (NF ₂)	V ₂	1.5	V
3 (V _{B2})	V ₂ V ₃	1.5	V
4 (BYPASS ₂)	V ₄	1.5	V
5 (MUTE)	V ₅	0	V
6 (BYPASS ₁)	٧6	2.2	V
7 (OUT ₂)	V ₆ V ₇	1.5	V
8 (GND)	٧g	0	V
9 (V _{CC})	V ₉	3.0	V
10 (OUT ₁)	V ₁₀	1.5	V
11 (V _{RF})	V ₁₁	2.3	V
12 (BASE)	V ₁₂	2.2	V
13 (PW ON/OFF)	V ₁₃	3.0	V
14 (V _{B1})	V ₁₄	1.5	V
15 (NF ₁)	V ₁₅	1.5	V
16 (IN ₁)	V ₁₆	1.5	V

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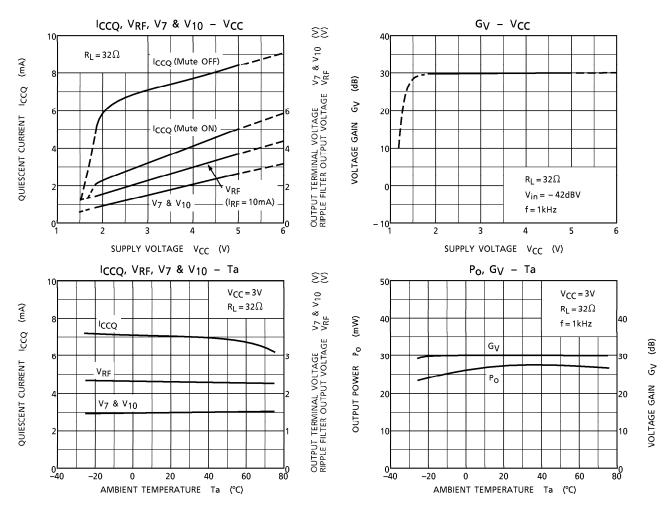
TEST CIRCUIT



Note: R_H: Protection resistance

C₆ & C₇: Tantalum capacitor or polyester film capacitor

C₅ : Tantalum capacitor



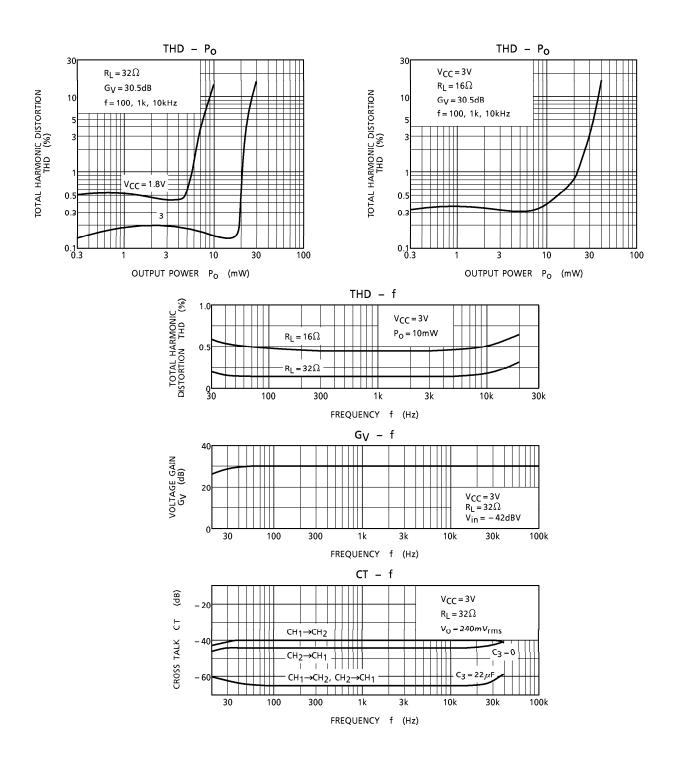
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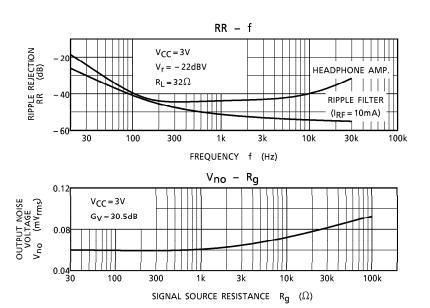
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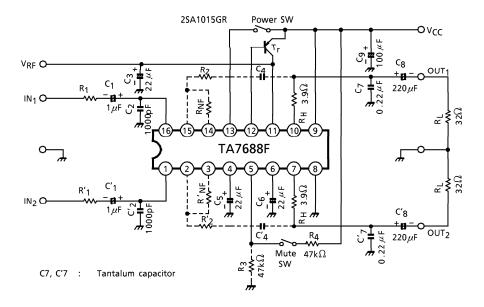
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APPLICATION CIRCUIT



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EXTERNAL PARTS TABLE (Mention only CH₁)

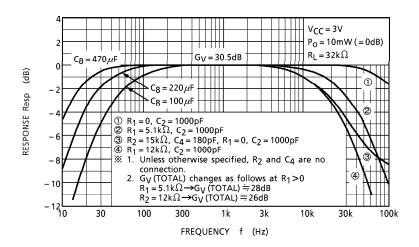
PARTS No.	TYPICAL	PURPOSE	INFLU SMALLER THAN TYP.	NOTE	
c ₁	1μF	Coupling	Bad low frequency response	"Pop" noise is high.	Input
C ₂	1000pF	LPF	$f_{CH} = \frac{1}{2\pi C_2 (R_1 // Z_{in})}$	Noise receiving protection	
R ₁	_			0 kHz) at R ₁ = 5.6k Ω 0 kHz) at R ₁ = 12k Ω	Equivalent signal source impedance
C ₃	22 μF	Decoupling for VRF	Stability (OSC) decreases, V _{no} at V _{RF} increases	(It is better to connect to input side GND)	Use tantalum capacitor
R _{NF}	1	G _V Adjustment	Not available at Gy- If necessary devide a resistors		_
R ₂	(15 $\mathbf{k}\Omega$)	f-response control, THD	- 3dB point is 20kHz Check ringing at clip		Low OSC margine at
C ₄	(180pF)	imperovement at high freq.	down.		G _V <40dB
C ₅	22 μ F	Bypass capacitor for bias	THD and V _{no} Degradation	_	It is better to connect to input side GND.
c ₆	22 μ F	Bypass capacitor for ripple filter	Ripple rejection ratio degradation	_	It is better to connect to output side GND.
R ₃	47k Ω	Pull down resistor at mute pin	ICC increases at mute ON	Pull down effect down	Additional resistor at long pattern only
R ₄	47k Ω	IMUTE limiter	IMUTE increases (Unnecessary at VCC = 3V)	I _{MUTE} decreases	I _{MUTE} <150μΑ
R _H	3.9Ω	Protection resistance. Phase compensation	Rush current increases. Phase compensation is out.	Output decreases. Phase compensation is out.	CR filter with C ₇
C ₇	0.22 μF	Phase compensation	Oscillation	THD degradation by load capaci- tance	Recommended to use tantalum or film capacitor
C ₈	220 μF	Coupling	Bad low frequency response	"P _{op} " noise is high.	Output
Cg	100μF	V _{CC} decoupling	Oscillation margin decreases	_	Necessary to be near pin 9
T _r	2SA1015GR	Booster for V _{RF}	_	_	To be added at I _{RF} >10mA

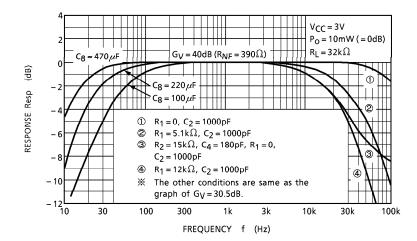
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1. f-Resp (Mention Only CH₁)





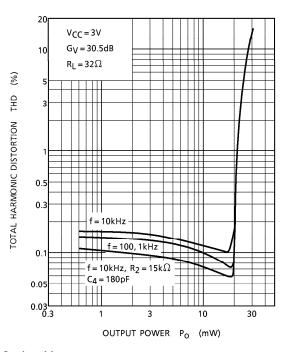
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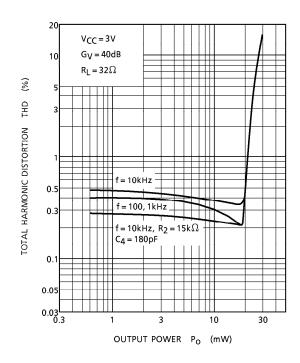
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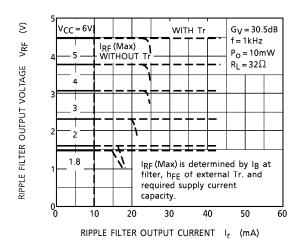
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2. Po-THD (Correspond to 1. f-Resp)





3. I_{RF}-V_{RF}



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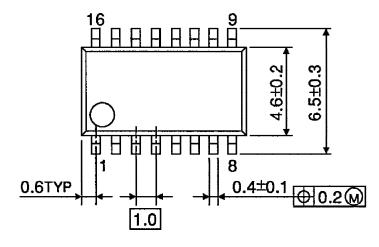
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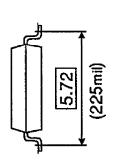
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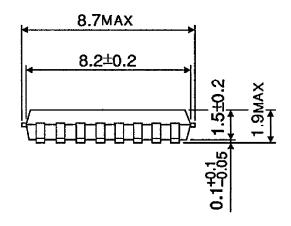
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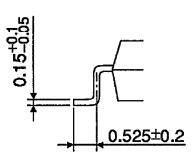


SSOP16-P-225A









Weight: 0.14g (Typ.)

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